TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

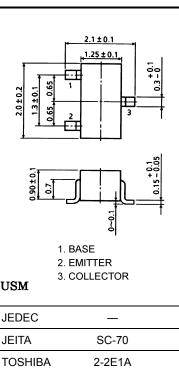
2SC4213

For Muting and Switching Applications

- High emitter-base voltage: $V_{EBO} = 25 V (min)$
- High reverse hFE: Reverse hFE = 150 (typ.) (VCE = -2 V, IC = -4 mA)
- Low on resistance: $RON = 1 \Omega$ (typ.) (IB = 5 mA)
- High DC current gain: h_{FE} = 200~1200
- Small package

Absolute Maximum Ratings (Ta = 25°C)

| Characteristics | Symbol | Rating | Unit |
|-----------------------------|------------------|---------|------|
| Collector-base voltage | V _{CBO} | 50 | V |
| Collector-emitter voltage | V _{CEO} | 20 | V |
| Emitter-base voltage | V _{EBO} | 25 | V |
| Collector current | Ι _C | 300 | mA |
| Base current | Ι _Β | 60 | mA |
| Collector power dissipation | P _C | 100 | mW |
| Junction temperature | Тј | 125 | °C |
| Storage temperature range | T _{stg} | -55~125 | °C |



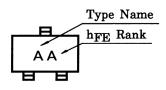
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the

Weight: 0.006 g (typ.)

reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Marking



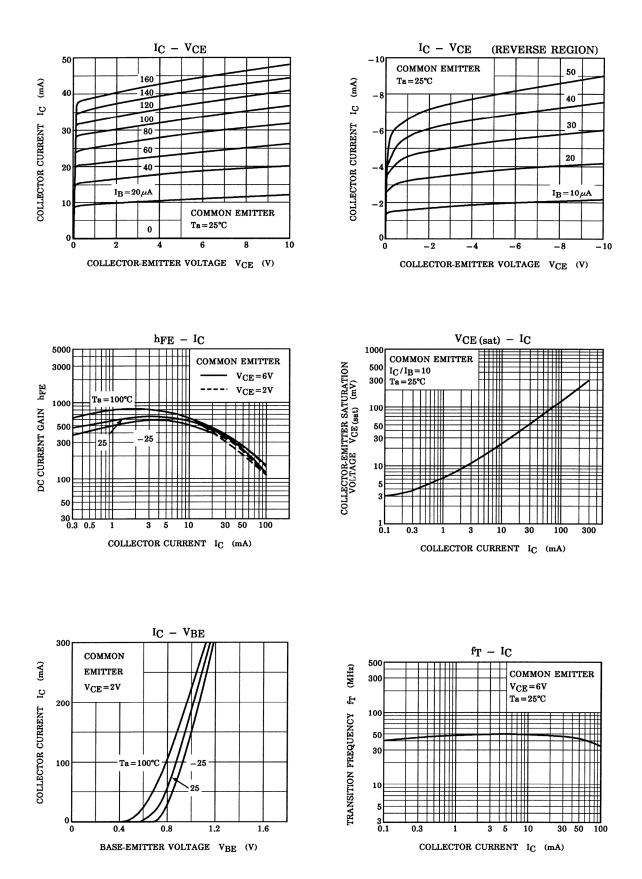
Unit: mm

Electrical Characteristics (Ta = 25°C)

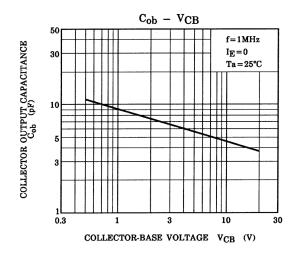
| Chara | acteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|------------------------------|--------------------|---------------------------|---|-----|-------|------|------|
| Collector cut-off c | current | I _{CBO} | $V_{CB} = 50 \text{ V}, \text{ I}_{E} = 0$ | _ | | 0.1 | μΑ |
| Emitter cut-off cu | rrent | I _{EBO} | $V_{EB} = 25 \text{ V}, \text{ I}_{C} = 0$ | _ | _ | 0.1 | μA |
| DC current gain | | h _{FE} (Note) | $V_{CE} = 2 V$, $I_C = 4 mA$ | 200 | _ | 1200 | |
| Collector-emitter | saturation voltage | V _{CE (sat)} | $I_{C} = 30 \text{ A}, I_{B} = 3 \text{ mA}$ | | 0.042 | 0.1 | V |
| Base-emitter volta | age | V _{BE} | $V_{CE} = 2 V$, $I_C = 4 mA$ | _ | 0.61 | _ | V |
| Transition freque | ncy | fT | $V_{CE} = 6 \text{ V}, \text{ I}_{C} = 4 \text{ mA}$ | _ | 30 | | MHz |
| Collector output capacitance | | C _{ob} | $V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$ | _ | 4.8 | 7 | pF |
| Switching time Sto | Turn-on time | t _{on} | $10V \prod_{1 \neq s} \frac{4k\Omega}{V_{BB}} \bigvee_{CC} = -3V = 12V$ | | 160 | _ | |
| | Storage time | t _{stg} | | | 500 | _ | ns |
| | Fall time | t _f | | | 130 | | |

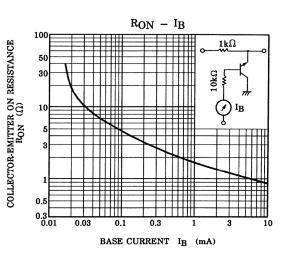
Note: hFE classification A: 200~700, B: 350~1200

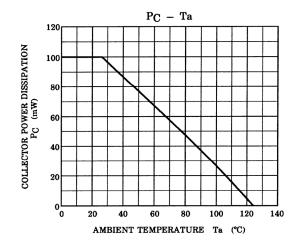
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20070701-EN GENERAL

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